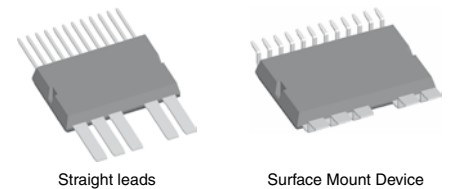
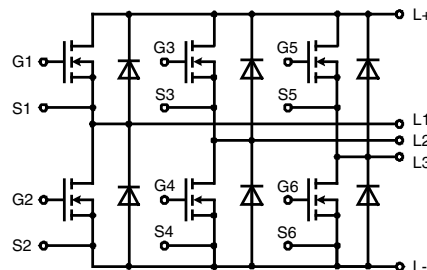


Three phase full Bridge with Trench MOSFETs in DCB isolated high current package

$$\begin{aligned} V_{DSS} &= 85 \text{ V} \\ I_{D25} &= 103 \text{ A} \\ R_{DSon \text{ typ.}} &= 5.5 \text{ m}\Omega \end{aligned}$$



MOSFETs			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	85	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	103	A
I_{D90}	$T_C = 90^\circ\text{C}$	77	A
I_{D110}	$T_C = 110^\circ\text{C}$	68	A
I_{F25}	$T_C = 25^\circ\text{C (diode)}$	tbd	A
I_{F90}	$T_C = 90^\circ\text{C (diode)}$	tbd	A
I_{F110}	$T_C = 110^\circ\text{C (diode)}$	tbd	A

Applications

- AC drives
 - in automobiles
 - electric power steering
 - starter generator
 - in industrial vehicles
 - propulsion drives
 - fork lift drives
- in battery supplied equipment

Features

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - high current capability 300 A max.
 - aux. terminals for MOSFET control
 - terminals for soldering or welding connections
 - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings

Package options

- 2 lead forms available
 - straight leads (SL)
 - SMD lead version (SMD)

Symbol	Conditions	Characteristic Values			
		$(T_J = 25^\circ\text{C, unless otherwise specified})$			
		min.	typ.	max.	
$R_{DSon}^{1)}$	on chip level at $V_{GS} = 10 \text{ V}; I_D = 75 \text{ A}$	$T_J = 25^\circ\text{C}$		5.5	$\text{m}\Omega$
		$T_J = 125^\circ\text{C}$		12.7	$\text{m}\Omega$
$V_{GS(th)}$	$V_{DS} = 20 \text{ V}; I_D = 250 \mu\text{A}$	2.0		4.0	V
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		5	μA
		$T_J = 125^\circ\text{C}$		100	μA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			0.2	μA
Q_g	$V_{GS} = 10 \text{ V}; V_{DS} = 42 \text{ V}; I_D = 75 \text{ A}$		114		nC
Q_{gs}			30		nC
Q_{gd}			35		nC
$t_{d(on)}$	inductive load $V_{GS} = 10 \text{ V}; V_{DS} = 42 \text{ V}$ $I_D = 75 \text{ A}; R_G = 39 \Omega;$ $T_J = 125^\circ\text{C}$		tbd		ns
t_r			tbd		ns
$t_{d(off)}$			tbd		ns
t_f			tbd		ns
E_{on}			tbd		mJ
E_{off}			tbd		mJ
E_{recoff}			tbd		mJ
R_{thJC}	with heat transfer paste (IXYS test setup)		1.3	1.0	K/W
R_{thJH}			1.6	1.6	K/W

¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + R_{Pin \text{ to Chip}})$

Source-Drain Diode

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_{SD}	(diode) $I_F = 100\text{ A}$; $V_{GS} = 0\text{ V}$		0.9	1.2
t_{rr}	$I_F = 100\text{ A}$; $-di_F/dt = 800\text{ A}/\mu\text{s}$; $V_R = 24\text{ V}$ $T_{VJ} = 125^\circ\text{C}$		tbd	ns
Q_{RM}			tbd	μC
I_{RM}			tbd	A

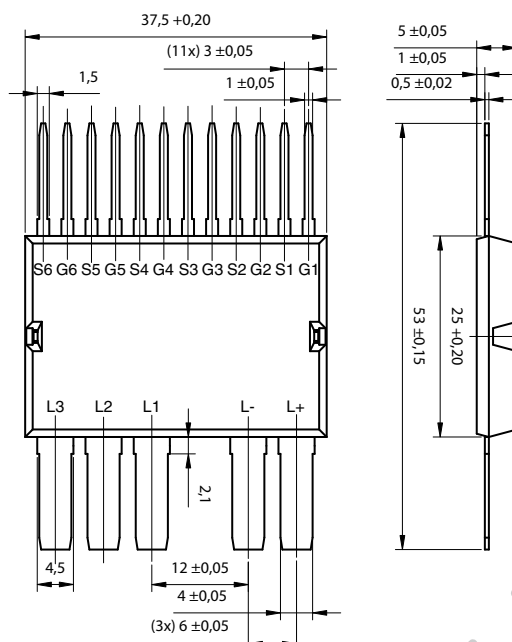
Component

Symbol	Conditions	Maximum Ratings	
I_{RMS}	per pin in main current paths (P+, N-, L1, L2, L3) may be additionally limited by external connections	300	A
T_J		-55...+175	$^\circ\text{C}$
T_{stg}		-55...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}$, 50/60 Hz, $f = 1\text{ minute}$	1000	V~
F_C	mounting force with clip	50 - 250	N

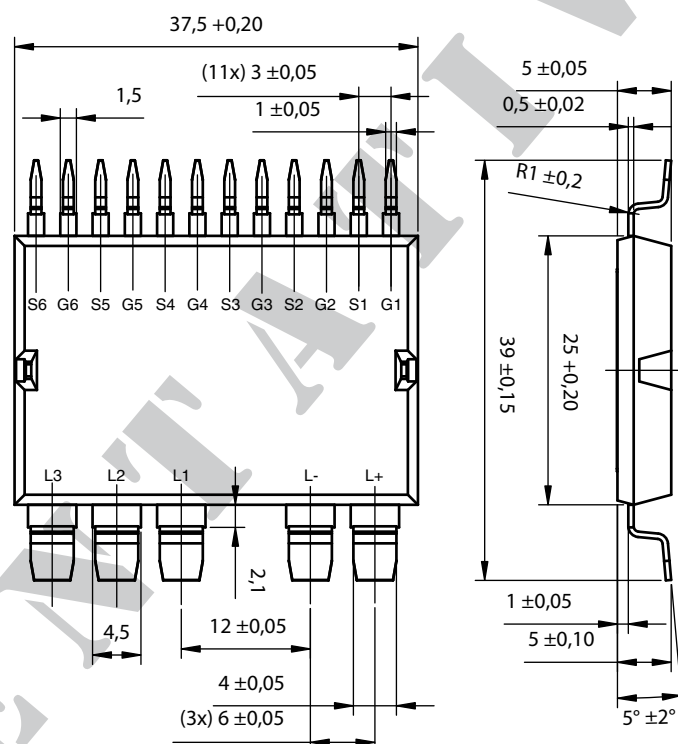
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin\text{ to chip}}^{1)}$	L+ to L1/L2/L3 or L- to L1/L2/L3		1.0	$\text{m}\Omega$
C_P	coupling capacity between shorted pins and mounting tab in the case		160	pF
Weight			25	g

¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + R_{Pin\text{ to Chip}})$

Straight Leads GWM 100-0085X1-SL



Surface Mount Device GWM 100-0085X1-SMD



Leads	Ordering	Part Name & Packing Unit Marking	Part Marking	Delivering Mode	Base Qty.	Ordering Code
Straight	Standard	GWM 100-0085X1 - SL	GWM 100-0085X1	Blister	28	tbd
SMD	Standard	GWM 100-0085X1 - SMD	GWM 100-0085X1	Blister	28	tbd